

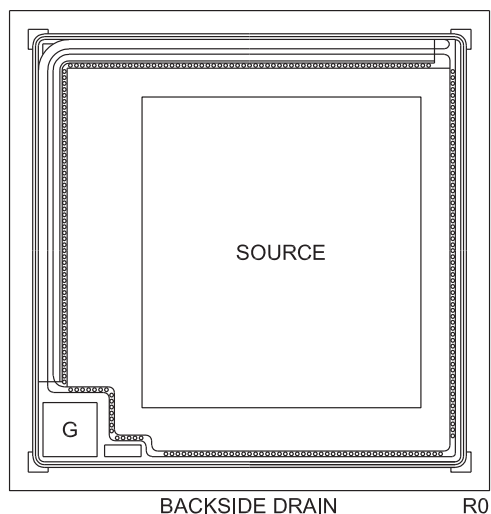
PROCESS CP379X
Small Signal MOSFET Transistor
N-Channel Enhancement-Mode Transistor Chip



PROCESS DETAILS

Die Size	31.5 x 31.5 MILS
Die Thickness	5.5 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	19.3 x 21.3 MILS
Top Side Metalization	Al-Si - 35,000Å
Back Side Metalization	Ti/Ni/Ag - 2,000Å/3,000Å/20,000Å

GEOMETRY



GROSS DIE PER 6 INCH WAFER

24,000

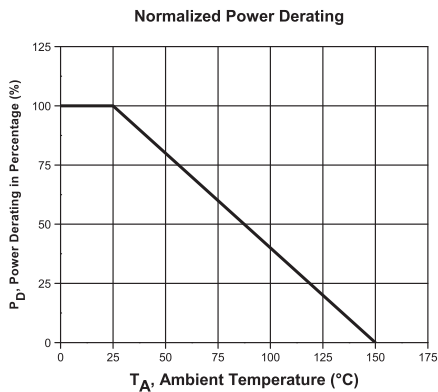
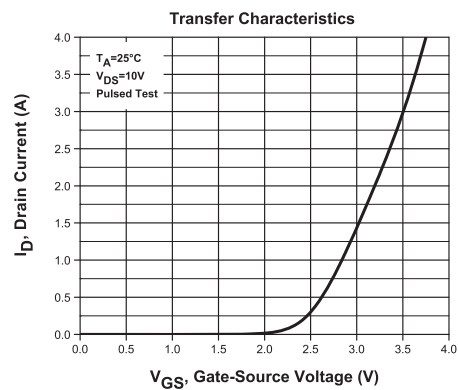
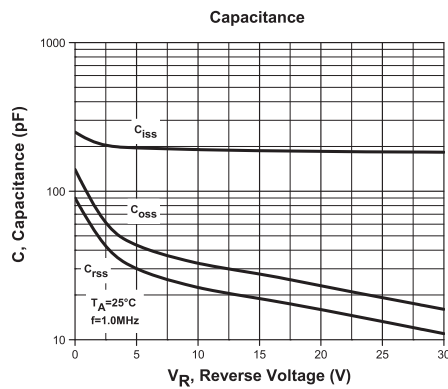
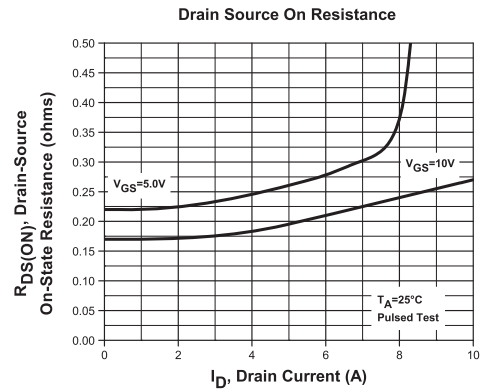
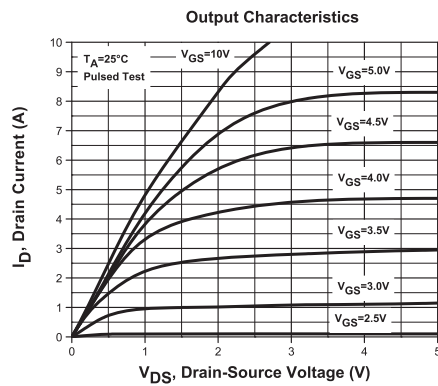
PRINCIPAL DEVICE TYPE

CMPDM7002AHC

R0 (20-September 2010)

PROCESS CP379X

Typical Electrical Characteristics



R0 (20-September 2010)